

Index

a

- ABAQUS 289, 304
 accelerator coverage, curvature enhanced,
 see CEAC
 activation
 – barrier 143
 – blocked electrodes 135–137
 – thermal 269–283
 active electronic devices 1–99
 additive processes 113–146
 adsorbates
 – deactivation 121
 – evolution 121–122
 – impact on microstructure 122–125
 – incorporated into growing deposit 119–121
 – inhibition of metal deposition 125–130
 – segregated 118–119
 adsorption
 – co-adsorption effects 134
 – competitive 135–137, 141–146
 – diffusion coefficient 117, 119–120
 – isotherms 220–221
 – kinetics 117
 – potential-dependent 144–145
 – spontaneous 221–223
 – SPS 143–146, 164
 – strong 118
 Airy's formula 9
 Al/Al₂O₃ system 53–54
 algorithms 303–311, 315, 317, 323–324
 – KMC, *see* KMC
 – shape change 146, 149, 164
 alkaline electrolytes 194
 alternative anode materials 73–74
 alternative dielectric materials 90–96
 amino functionalized porphyrin 224
 amino groups 138
 amorphous films 2–4, 17
 – Al/Al₂O₃ 54
 – anodically formed oxides 48
 – Beilby layer 40
 – capacitor devices 67–70
 – SiO₂ 75, 89
 – Ta₂O₅ 53, 65
 – TiO₂ 19, 23, 25, 40–41, 95
 – ZrO₂ 42–46
 anisotropic etching 86–89
 anisotropic parameters 40
 anisotropy
 – optical 38, 48
 – spectroscopic anisotropy micro-ellipsometry,
 see SAME
 annealing
 – rapid thermal 92–94, 299, 317–320
 – simulated 315
 – thermal 69
 anode materials, alternative/modified 73–74
 anode sinter body, thermal conductivity
 71–72
 anodic ETR current density 35
 anodic formation factor 3
 anodic oxide formation 6, 29, 45, 51, 56, 64
 – irreversible 55
 – Nb/Nb₂O₅ system 49
 anodic oxide growth 37
 anodic passivation 76
 anodic passive layer formation, single Ti
 grains 28–30
 anodizing 64
 applications
 – electrochemical 297–298
 – electrolytic capacitor manufacturing 57–74
 – laser in electrochemistry 8–10
 – microelectronic 295–296
 – Nb/Nb₂O₅ system 53
 – photoresist microelectrodes 28–35

- Si/SiO₂ system 77–90
- Zr/ZrO₂ system 44–46
- aqueous electrolytes 193–199
 - pH 197–199
- aspect ratio 27
- DT Si etch 84–85
- avalanche effects, electronic 67

- b**
- band gap energy 3, 15
- band structure 8, 28, 37, 52
- barrier, activation 143
- battery behavior 58
- Bayesian estimation 312
- Beer, Lambert–Beer’s law 13–14
- Beilby layer, isotropic 40
- ‘Best’-cell DRAM 83
- bit-line design, folded 81
- Blue Ribbon Panel report 290–291
- bond insertion mechanism 321
- boron dopant profiles 319
- bottle-shaped DT 85–88
- boundary, moving 309
- boundary layer
 - diffusion 28
 - hydrodynamic, *see* hydrodynamic boundary layer thickness
 - thickness 154, 156, 161, 174
- break down voltage 62
- brightening 111–112
 - catalyst-derived 161–176
- bump formation, attenuation 177
- Butler–Gärtner model 10–11
- Butler–Volmer equation 238
- Butler–Volmer kinetics 147

- c**
- $C(U)$ curve, valve metal electrodes 7–8
- Cabrera–Mott interface 6–7
- capacitance
 - density 80
 - measurements 30–33
- capacitors
 - ceramic 62
 - device types 62–65
 - DRAM storage 82–90
 - electrolytic, *see* electrolytes
 - fundamentals 57–62
 - manufacturing 57–74
 - Nb/Nb₂O₅ 53
 - polymer foil 62
 - Ta 62–66
- carbon electrode, glassy 205, 217
- catalysis
 - electro-, *see* electrocatalysis
 - metal deposition 134
 - catalyst-derivatized electrodes 138–141
 - catalyst-derived brightening 111–112, 161–176
 - stability analysis 173–176
 - catalyst-free electrolyte 165, 167
 - catalysts
 - Cl 135
 - competitive adsorption 135–137
 - evolution 143
 - function and consumption 139–143
 - PEG–SPS–Cl 138, 141–144, 175
 - cathode material, conductive polymers 72–73
 - cathodic ETR current density 35
 - cation transfer coefficient 3
 - CEAC (curvature enhanced accelerator coverage) 111–113, 118, 161, 169–178
 - cell
 - DRAM 80
 - electrochemical 4
 - ceramic capacitors 62
 - multi-layer 62
 - ceramic oxides, as dielectric films 1–99
 - charge transfer kinetics, site dependence 142–143
 - CHARMM 304
 - chelate structures 191, 244
 - chemical rate-determining step 243–244
 - chemical vapor deposition, *see* CVD
 - chemically modified electrodes 221–232
 - redox active 232–241
 - chip manufacture, electrochemical processing 293
 - chronoamperometry 137–140, 206
 - chronocoulometric plots 206–207
 - CMOS (complementary metal oxide semiconductor) 77, 79
 - co-adsorption effects 130–134
 - co-deposition 125
 - Co porphyrins
 - dioxygen reduction 252–259
 - single-ring 256–259
 - *trans*-[Co([14]aneN₄)(OH₂)₂]³⁺ 212–216
 - coarse-grained simulation methods 303–304
 - Co(III)(cyclam) 202, 204, 206, 212–216
 - competitive adsorption 135–137, 141–146
 - competitive interactions 122
 - complex dielectric constant 59
 - complex systems 289
 - conductive polymers, cathode material 72–73
 - conductivity, thermal 71–72
 - confidence intervals 315
 - consumption, catalysts 137–141

- consumption processes 117–121
 - continuum methods 300
 - CoPI 253–255
 - cyclic voltammogram 253
 - corrosion resistance 1
 - covalent attachment 223–225
 - critical wavenumber 175
 - crystallization nuclei 68
 - crystallographic orientation 17–18
 - current
 - leakage, *see* leakage current
 - limiting 206, 250, 264
 - photo-, *see* photocurrent
 - plateau 215, 249–251
 - Poole–Frenkel 89
 - threshold 160
 - current density
 - diffusion-limited 143
 - effect on microstructure 123
 - ETR 35
 - curvature enhanced accelerator coverage, *see* CEAC
 - CVD (chemical vapor deposition) 2, 75, 89–96
 - cyberinfrastructure 311
 - cyclic voltammogram 20, 28–30
 - Al/Al₂O₃ system 53–54
 - anodic passivation 76
 - capacitor devices 58–59
 - conductive polymers 73
 - CoPI 255
 - Fe(III)TMPyP 205, 210–211, 217
 - Hf/HfO₂ system 46–47
 - Nafion 226–227
 - Nb/Nb₂O₅ system 49
 - thermally activated macrocycles 280
 - Zr/ZrO₂ system 38, 43–44
- d**
- D-optimal design 313
 - Damascene copper process 163
 - data collection, high-throughput 315
 - deactivation, adsorbates 121
 - Debye length 35, 57
 - deep trench, *see* DT
 - defect state density 38, 51, 57
 - defraction analysis, X-ray 53–54
 - density
 - capacitance 80
 - current, *see* current density
 - defect state 38, 57
 - donor 30–34, 36–37
 - deoxidization 68
 - depassivation, potential-dependent 131
 - deposit, growing 119–121
 - deposition
 - co- 125
 - electro-, *see* electrodeposition
 - metals, *see* metal deposition
 - design
 - D-optimal 313
 - electrochemical systems 289–324
 - molecular 259, 320
 - multiscale model-based 315–322
 - desorption 117, 121–122, 302, 307
 - hydrocarbon 93
 - slow 223
 - destabilizing influences, superconformal film growth 108–110
 - device simulation 298–299
 - DHE (dynamic hydrogen reference electrode) 282, 284
 - dicobalt porphyrin dimers 266
 - dielectric constant 92–95
 - Al/Al₂O₃ system 53
 - capacitance measurements 30–31
 - complex 59
 - Hf/HfO₂ system 47–48
 - Nb/Nb₂O₅ system 49, 52–53
 - relative, *see* relative dielectric constant
 - Ta/Ta₂O₅ system 56
 - Zr/ZrO₂ system 44, 46
 - dielectric films
 - experimental approaches 2–5
 - for electronic devices 1–99
 - dielectric materials
 - alternative 90–96
 - Ta₂O₅ 92–95
 - dielectrics, nano- 1–2
 - nano- 97
 - differential pulse voltammetry 225, 238
 - diffuse double layer 7
 - diffusion
 - boundary layer 28
 - lateral hole 24
 - diffusion coefficient 28, 155, 158, 159, 301
 - adsorption 117, 119–120
 - electrocatalysis 204–205
 - transition metal macrocycles 211–212
 - diffusion equation 148
 - diffusion-limited current density 143
 - dimers, dicobalt porphyrin 267
 - dioxygen reduction 191–284
 - Co porphyrins 252–259
 - electrocatalytic aspects 241–268
 - in aqueous electrolytes 193–199, 212–219
 - macrocyclic-mediated 212–219
 - ring functionalization 252–259

- dipping, single step 72
- direct leakage current 65
- direct tunneling 35, 81
- disc electrode, rotating, *see* RDE
- dislocation formation, Ta capacitors 67–70
- dissipation factor 60
- donor density 30–34, 36–37
- dopant profiles, boron 319
- doping 63, 70
 - poly-Si 87, 96
 - Si/SiO₂ system 75, 77, 83–84, 89
 - sidewall 95
 - Ti/TiO₂ system 36
 - V- 51
- double layer, diffuse 7
- DRAM (dynamic random access memory)
 - ‘Best’-cell 83
 - cell 80
 - operation 81–82
 - Si/SiO₂ system 80–82
 - stack-capacitor 91
 - storage capacitor 82–90
- droplet method, nanoliter 25–28
- DT (deep trench) 82–90
 - bottle-shaped 85–88
 - etching aspect ratio 84–85
- dynamic hydrogen reference electrode (DHE) 282, 284
- dynamic polarization curves 197, 198–208, 213, 245, 254–257
- dynamically coupled multiscale simulation 307–309
- dynamics
 - Langevin 301
 - molecular 300–302, 303–304
 - redox 238–241
- e**
- ECE (electrochemical–chemical–electrochemical) mechanism 241
- ECR (electron cyclotron resonance) 92–93
- electrical capacitance, *see* capacitance
- electrical/electrical micro-methods 5
- electrical method class, photocurrent measurements 10–15
- electrocatalysis 192–193
 - diffusion coefficient 211–212
 - dioxygen reduction 241–268
 - heterogeneous, *see* heterogeneous electrocatalysis
 - homogeneous, *see* homogeneous electrocatalysis
- electrocatalysts
 - Co(III)(cyclam) 202, 204, 206, 212–216
 - Fe(III)TMPyP 203–212, 216–219, 252
 - metalloporphyrins 203
 - phthalocyanines 191, 199, 244–247
 - porphyrins, *see* porphyrins
 - Pt-based 191, 196, 259
 - transition metal macrocycles 191–284
- electroceramic thin film dielectrics 46
- electrochemical applications
 - laser 8–10
 - multiscale modeling 297–298
- electrochemical cell 4
- electrochemical–chemical–electrochemical (ECE) mechanism 241–243
- electrochemical measurements
 - modified electrodes 221–226
 - redox active electrodes 232–233
 - thermally activated macrocycles 280
- electrochemical metrics 135
- electrochemical oxide layer formation 5–7
- electrochemical photocurrent measurements 10–15
- electrochemical potential 1
- electrochemical processing, chip manufacture 293
- electrochemical rate-determining step 243
- electrochemical systems, design 289–324
- electrodeposition 108–116, 121–122
 - multiscale modeling 310, 315
- electrodes
 - blocked 135–137
 - catalyst-derivatized 138–141
 - chemically modified 221–232
 - DHE 282, 284
 - glassy carbon 205, 217
 - macroscopic single crystal 29
 - OTTLE 232–241
 - photoresist micro-, *see* photoresist microelectrodes
 - redox active 232–241
 - rotating disc, *see* RDE
 - rotating ring-disk, *see* RRDE
 - standard hydrogen, *see* SHE
 - Teflon-bonded 279
 - thin porous coating 270–271
- electrohydrodynamic impedance spectroscopy 127
- electrolytes
 - alkaline 194
 - anodic passivation 76
 - aqueous, *see* aqueous electrolytes
 - capacitance measurements 30, 46–47, 55
 - catalyst-free 165, 167
 - electrochemical measurements 16, 18, 25, 28

- electrolyte capacitors 1, 37, 52–54, 97
 - interfaces 6–7, 19, 36
 - manufacturing of electrolyte capacitors 57–74
 - PEG–SPS–Cl 108, 144, 164, 170, 178
 - solid 64
 - SPS adsorption 143–146
 - electron cyclotron resonance (ECR) 92–93
 - electron-donating groups 256–259
 - electron polarization 59
 - electron spin resonance spectra 203
 - electron transfer, heterogeneous 211–212
 - electron transfer reaction, *see* ETR
 - electronic applications
 - Nb/Nb₂O₅ 53
 - ZrO₂ applications 44–46
 - electronic avalanche effects 67
 - electronic devices, active/passive 1–99
 - electronic properties, modified
 - electrodes 227–229
 - ellipsometry, spectroscopic anisotropy micro-, *see* SAME
 - energy
 - band gap 3, 15
 - mobility gap 19
 - engineering science, simulation-based 290–291
 - ESR (equivalent series resistance) 60–61, 73
 - estimation, Bayesian 312
 - etched foil technology 54, 64
 - etching 5
 - anisotropic 85
 - aspect ratio 84–85
 - RIE 84–86
 - Si/SiO₂ system 83, 85–89, 91, 95
 - etching aspect ratio, DT (deep trench) 84–85
 - ETR (electron transfer reaction) 34–35, 238–241
 - evolution
 - adsorbates 121–122
 - catalysts 143
 - morphological 146–178
- f**
- face-to-face porphyrins 259–268
 - feature filling
 - catalyst-derived brightening 161–173
 - geometric leveling 153–159
 - Fe(III)TMPyP 203–212, 216–219, 251
 - cyclic voltammogram 205, 210, 217
 - Fermi level pinning 75
 - ferroelectrics 1, 90–91
 - field effect transistors, metal oxide semiconductor, *see* MOSFETs
 - filling 153–159
 - simulation 148
 - super-, *see* superfilling
 - film
 - amorphous, *see* amorphous films
 - dielectric 2–5
 - HfO₂ 48
 - monolayer 115
 - superconformal growth, *see* superconformal film growth
 - TiO₂ 19–21
 - ultra-thin amorphous 11–15
 - film thickness 4, 10–11, 14–15, 18–22, 97
 - effect on microstructure 123–124
 - Hf/HfO₂ system 47
 - Nb/Nb₂O₅ system 49–51
 - Ta/Ta₂O₅ system 56–57
 - variation 53
 - Zr/ZrO₂ system 40, 44
 - *see also* layer thickness
 - fluent 300
 - fluid dynamics codes 324
 - folded bit-line design 81
 - formal redox potential 204–209
 - formation factor 18, 42
 - anodic 3
 - HfO₂ 47
 - Nb/Nb₂O₅ system 49
 - oxide, *see* oxide formation factor
 - Ta/Ta₂O₅ system 46
 - Fowler–Nordheim tunneling 81
 - Frenkel, Poole–Frenkel current 79
 - Frumkin isotherm 117
 - functional groups 225
 - functionalization, ring 252–259
- g**
- galvanostatic oxide growth 7
 - gap energy
 - mobility 19
 - *see also* band gap energy
 - Gärtner, Butler–Gärtner model 10–11
 - gate length 77, 79–80
 - Gaussian temperature distribution 9
 - geometric leveling 110, 150–152
 - stability analysis 160–161
 - glassy carbon electrode 205
 - grain orientation, Ti substrate 17–18
 - grain refinement 111–112
 - grains, hemispherical Si, *see* HSG
 - green body uniformity 72
 - groove
 - hemi-cylindrical 162
 - semicircular 152

- V-notch 151
- groups
 - amino 138
 - electron-donating 256–259
 - functional 225
 - hydroxyl 7
 - redox 256–257
- growing deposit, adsorbates 119–121

h

- hcp (hexagonal closed package) 39, 48
- heat accumulation 66
- Helmholtz layer 7, 19
- hemi-cylindrical groove 162
- hemin, *see* Hm
- hemispherical Si grains, *see* HSG
- heterogeneity, Ti/TiO₂ system 15
- heterogeneous electrocatalysis 203, 219–268
 - model systems 244–269
 - pH 234–238, 246–255
- heterogeneous electron transfer, reaction rates 211–212
- heterogeneous oxygen reduction 194
- hexagonal closed package (hcp) 39, 48
- Hf/HfO₂ system 46–48
- HfO₂, film formation 48
- high-field equation 6
- high-field model 6
- high-throughput data collection 315
- highest occupied molecular orbitals (HOMO) 201, 267–268
- Hm (hemin) 221–224, 229, 233–236
- hole diffusion, lateral 24
- hole migration 19
- HOMO (highest occupied molecular orbitals) 201, 267–268
- homogeneous electrocatalysis 202–219
 - model systems 212–219
- HSGs (hemispherical Si grains) 85, 94
 - formation 89–90
- hydrodynamic boundary layer thickness 110, 117, 126, 128
- hydroxyl groups 7
- hysteretic voltammogram 136

i

- ICs (integrated circuits) 77, 96–97, 291, 294
 - molecular simulation 298–299
- impedance 60
 - optical 240
- implantation, ion 317
- impurity concentration 142
- in situ* microscopic sample monitoring 4
- in situ* spectroscopy 281–283

- modified electrodes 226–232
- inhibition
 - metal deposition 125–130
 - PEG 130
- inhibitor-based leveling 110–111, 152–161
- inhibitor flux 126
- instabilities, oscillatory 176
- integrated modeling 296
- integrated pyrolysis–mass spectra 276
- interface
 - non-planar 161
 - solid–liquid 307
- interface motion 146–178
- internal reflections, multiple 12
- internally coupled moving boundary 309
- intra-layer transport 109
- intrinsic charge carrier mobility 74
- ion implantation 317
- ionic polarization 59
- $i_{ph}(U)$ measurements 18–19
- iron tetrakis(*N*-methyl-4-pyridyl) porphyrin 216–219
- iron(III) protoporphyrin IX chloride (hemin), *see* Hm
- isotherms
 - adsorption 220–221
 - Frumkin 117
 - Langmuir 117
- isotropic Beilby layer 40

k

- kinetics
 - adsorption 117
 - Butler–Volmer 147
 - charge transfer 142–143
 - Langmuir 117, 143, 164
- KMC (kinetic Monte Carlo) simulation 300, 304, 307, 309
- Koutecky–Levich plot 251, 255

l

- Lambert–Beer’s law 13–14
- Langevin dynamics 301
- Langmuir isotherm 117, 120, 128, 154
- Langmuir kinetics 117, 143, 164
- Laplacian diffusion equation 148
- laser scanning
 - TiO₂ films 19–21
 - UV- 21–22
- lasers
 - electrochemistry applications 8–10
 - thermal effects 9–10
- lateral hole diffusion 24
- laws and equations

- Airy’s formula 9
 - Butler–Volmer equation 238
 - high field equation 6
 - Langmuir isotherm, *see* Langmuir isotherm
 - Langmuir kinetics 117
 - Laplacian diffusion equation 148
 - Master equation 302
 - partial differential-algebraic equations 300–302
 - Poisson equation 7
 - Randles–Sevcik equation 218
 - Schottky–Mott equation 31–32
 - time-dependent diffusion equation 148
 - layer
 - diffuse double 7
 - diffusion boundary 28
 - Helmholtz 7, 19
 - isotropic Beilby 40
 - nano-crystalline 42
 - space charge 7, 13, 57
 - layer formation
 - anodic passive 28–30
 - electrochemical 5–7
 - layer thickness
 - boundary, *see* boundary layer thickness
 - hydrodynamic boundary, *see* hydrodynamic boundary layer thickness
 - *see also* film thickness
 - leakage current 65–66, 79, 89–90
 - capacitors 62
 - direct 65
 - Nb/Nb₂O₅ capacitors 53
 - Ta/Ta₂O₅ system 93–95
 - leakage node 90
 - leakage paths 46, 65, 67–68, 70–71, 77
 - length scales 176–178
 - multiple 293
 - leveling
 - geometric 110, 150–152
 - inhibitor-based 110, 111, 153–161
 - leveling power 153–155
 - Levich plot 251, 255
 - limiting current 206, 250, 264
 - locodynamic experiment 22
 - LUMO (lowest unoccupied molecular orbital) 201
- m**
- macrocycles
 - monomeric 225, 259
 - ruthenation 257
 - transition metal, *see* transition metal macrocycles
 - (un)metallated 200
 - macrocylic-mediated dioxygen reduction 212–219
 - macroscopic single crystal electrodes 29
 - mass conservation 118–120
 - mass spectrometry, pyrolysis 274–276
 - Master equation 304
 - MD (molecular dynamics) 300–301, 303–304
 - measurements
 - capacitance 30–33
 - electrochemical photocurrent 10–15
 - ETR 34–35
 - $i_{\text{ph}}(U)$ 18–19
 - transient 33–34
 - memory, dynamic random access, *see* DRAM
 - MEMS (microelectromechanical systems) 107, 297–298, 306
 - meso*-ring position 259
 - metal deposition
 - effect of competitive adsorption 141–146
 - inhibition 125–130
 - metal oxide semiconductor field effect transistors, *see* MOSFETs
 - metallated macrocycles 200
 - metalloporphyrins 203
 - metals
 - transition metal, *see* transition metal
 - valve, *see* valve metals
 - metrics, electrochemical 135
 - micro-ellipsometry, spectroscopic anisotropy, *see* SAME
 - micro-methods 4–5
 - micro-reflection spectroscopy, modified TiO₂ films 22–23
 - microelectrochemistry, photoresist 25–28
 - microelectrodes, photoresist, *see* photoresist microelectrodes
 - microelectromechanical systems (MEMS) 107, 297–298, 306
 - microelectronic applications, multiscale modeling 295–296
 - microfluidics 298, 306
 - micromanipulators 26
 - microscopic control 25–26
 - microscopic modification, TiO₂ films 19–21
 - microscopic sample monitoring, *in situ* 4
 - microstructure, impact of segregating adsorbates 122–125
 - migration, holes 19
 - mobility, intrinsic charge carrier 74
 - mobility gap energy 19
 - model systems
 - heterogeneous electrocatalysis 244–269
 - homogeneous electrocatalysis 212–219
 - modeling

- hierarchy 296
 - integrated 296
 - multiscale, *see* multiscale modeling
 - modified anode materials 73–74
 - modified TiO₂ films 21–25
 - molar paramagnetic susceptibility 212
 - molecular design 259, 320
 - molecular dynamics (MD) 300–301, 303–304
 - molecular nanotechnology 297
 - molecular orbitals 201
 - molecular simulation 298–304
 - coarse-grained methods 303–304
 - ICs 298–299
 - methods 300–302
 - molecular speciation
 - pH 209–212
 - transition metal macrocycles 207–211
 - monolayer films 115
 - monomeric macrocycles 225, 259
 - morphological evolution 146–178
 - MOSFETs (metal oxide semiconductor field effect transistors) 300
 - Hf/HfO₂ system 46
 - Si/SiO₂ system 77–80
 - Mossbauer effect spectroscopy 276–277
 - Mott
 - Cabrera–Mott interface 6–7
 - Schottky–Mott, *see* Schottky–Mott
 - moving boundary, internally coupled 309
 - multicycle voltammetry 144
 - multilayer ceramic capacitors 62
 - multiple internal reflections 12
 - multiple length scales 293
 - multiple time scales 293
 - multiscale modeling 289–334
 - challenges 310–315
 - electrodeposition 310, 314
 - rough surfaces 314
 - multiscale simulation 291–293, 304–309
 - dynamically coupled 307–309
 - multiscale systems engineering 291
 - multistep optimization 316
- n**
- Nafion, cyclic voltammogram 226–227
 - nanocrystalline layer 42
 - nanodielectrics 1–2, 97
 - nanolaminate component 46
 - nanoliter droplet method 25–28
 - nanopipette 25
 - nanoscale devices 291
 - nanoscale science 296–297
 - nanotechnology 77
 - molecular 298
 - Nb/Nb₂O₅ system 49–53
 - nitridation, rapid thermal 90
 - node leakage 90
 - non-planar interface 161
 - Nordheim, Fowler–Nordheim tunneling 81
 - NSF Blue Ribbon Panel report 290–291
 - nuclei, crystallization 68
- o**
- optical anisotropy 38, 48
 - optical/chemical micro-methods 5
 - optical/electrical micro-methods 5
 - optical impedance 240
 - optical method class, photocurrent measurements 10–15
 - optical/optical micro-methods 4–5
 - optically transparent thin layer electrode (OTTLE) 207–211
 - optimization, multistep 316
 - oscillatory instabilities 176
 - OTTLE (optically transparent thin layer electrode) 207–211
 - overpotential 139–141, 144–147, 173–175
 - oxidation, anodic 29
 - oxide collar 85
 - oxide formation
 - anodic, *see* anodic oxide formation
 - potentiodynamic, *see* potentiodynamic oxide formation
 - potentiostatic, *see* potentiostatic oxide formation
 - oxide formation factor 7, 44–45, 53
 - oxide growth
 - anodic 37
 - galvanostatic 7
 - oxide layer formation, electrochemical 5–7
 - oxygen content, Ta capacitors 67–70
 - oxygen reduction
 - heterogeneous 194
 - polarization curves 271–274
- p**
- paramagnetic susceptibility, molar 212
 - partial differential-algebraic equations 298–300
 - passivation, anodic 76
 - passive electronic devices 1–99
 - passive layer formation, anodic 28–30
 - PECVD (plasma-enhanced CVD) 92–93, 96
 - PEG (poly(ethylene glycol)) 130–146, 161, 164–166, 173–178, 313–314
 - inhibition 130
 - permittivity of a vacuum 59
 - perovskite structure 1

- pH 146
 - aqueous electrolytes 193–199
 - heterogeneous electrocatalysis 219–220
 - interfacial shifts 124
 - molecular speciation 212
 - photocorrosion 22
 - photocurrent measurements, electrochemical 10–15
 - photocurrent model, ultra-thin amorphous films 11–15
 - photocurrent spectra
 - Ti/TiO₂ system 18–19
 - Zr/ZrO₂ system 42–43
 - photoelectrochemistry 10–15
 - photoelectron spectroscopy, X-ray, *see* XPS
 - photoresist microelectrochemistry, modified TiO₂ films 25–28
 - photoresist microelectrodes
 - Ti/TiO₂ system 28–35
 - Zr/ZrO₂ system 43–44
 - phthalocyanines 191, 199
 - transition metal 244–247
 - physical vapor deposition, *see* PVD
 - pinning 17
 - Fermi level 75
 - pitting 36
 - plateau current 215, 248–251
 - plating, through-mask 116
 - Poisson equation 7
 - polarization 59
 - polarization curves
 - dynamic, *see* dynamic polarization curves
 - oxygen reduction 271–274
 - steady state 198, 249
 - steady state ring–disk 272–273
 - polycrystalline samples 16
 - poly(ethylene glycol), *see* PEG
 - polymers
 - conductive 72–73
 - foil capacitors 62
 - Poole–Frenkel current 89
 - porous coating electrodes, thin 269, 271
 - porphyrins 191–193, 199, 247–252
 - amino functionalized 224
 - Co, *see* Co porphyrins
 - dimers 266
 - face-to-face 259–268
 - iron tetrakis(*N*-methyl-4-pyridyl)porphyrin 216–219
 - metallo- 203
 - potential
 - electrochemical 1
 - formal redox 204–209
 - over- 141
 - standard reduction 193, 195
 - potential-dependent adsorption 144–145
 - potential-dependent depassivation 131
 - potential-step experiment 33
 - potentiodynamic oxide formation 2, 98
 - Al/Al₂O₃ 53
 - Nb/Nb₂O₅ 49
 - Ta/Ta₂O₅ 55
 - Ti/TiO₂ 27–28, 30–34
 - Zr/ZrO₂ 37–38, 40–41, 44
 - potentiostatic oxide formation 2
 - growth texture dependence 70
 - Ta/Ta₂O₅ 55
 - Zr/ZrO₂ 30–31, 33, 37, 44
 - Pourbaix diagram 51
 - precipitation 224
 - process simulation 298–299
 - production, Ta capacitors 62–65
 - protonation 267
 - Pt-based electrocatalysts 192
 - pulse voltammetry, differential 225
 - purity improvement 69
 - PVD (physical vapor deposition) 2, 75–76, 91, 94
 - pyrolysis-mass spectrometry 274–276
 - β-pyrrole position 255, 259–260, 264
- q**
- QM (quantum mechanical) simulation 300, 305–306
 - quantum yield 18–20
 - quasi-*in situ* spectroscopy 281–283
 - quasi-isothermal conditions 9
- r**
- radiation, synchrotron 230
 - radiotracer analysis 121
 - Randles–Sevcik equation 218
 - random access memory, dynamic, *see* DRAM
 - rapid thermal annealing 93, 299, 317–319
 - rapid thermal nitridation 90
 - rate-determining step 243
 - RDE (rotating disc electrode) 126, 196, 206, 214
 - heterogeneous electrocatalysis 221–222
 - reaction rates, heterogeneous electron transfer 211–212
 - reactive ion etching 84–86
 - rectifying effect 5–6
 - redox active chemically modified electrodes 232–241
 - redox dynamics 238–241
 - redox groups 256–258
 - redox potential, formal 205–209

- redox speciation 235–238
 - reduction
 - dioxygen, *see* dioxygen reduction
 - standard potential 193, 195
 - reflectance, UV–visible 233
 - reflection spectroscopy, micro- 22–23
 - reflections, multiple internal 12
 - relative dielectric constant 1–3, 44
 - resistance, corrosion 1
 - resonance tunneling 35
 - retention time 61
 - RIE (reactive ion etching) 84–86
 - ring-disk polarization curves, steady state 271–273
 - ring functionalization, dioxygen reduction 252–259
 - meso*-ring position 258
 - ripple voltage 62
 - rough surfaces 109
 - multiscale modeling 314
 - RRDE (rotating ring-disk electrode) 196–199, 213
 - heterogeneous electrocatalysis 221–222
 - runaway, thermal 70–74
 - ruthenation, macrocycles 257
 - rutile, *see* TiO₂
- S**
- SAME (spectroscopic anisotropy micro-ellipsometry) 4
 - grain orientation determination 17–18
 - modified TiO₂ films 23–25
 - Zr/ZrO₂ system 38–42
 - sample monitoring, *in situ* microscopic 4
 - scanning, laser, *see* laser scanning
 - Schottky–Mott analysis 51, 56, 97
 - Schottky–Mott behavior 37, 50
 - Schottky–Mott chart/plot 30–32, 56
 - Schottky–Mott equation 31–32
 - Schottky–Mott relationship 8
 - seam formation 170
 - Secvik, Randles–Secvik equation 218
 - segregation, surface 117–121
 - self-discharge time 61
 - self-healing mechanism 66
 - semicircular groove 152
 - semiconductors 74
 - sense amplifier 81
 - shallow trench isolation, *see* STI
 - shape change
 - algorithms 149
 - simulation 146–150, 167
 - SHE (standard hydrogen electrode) 16
 - Si grains, hemispherical, *see* HSG
 - Si oxides, as dielectric films 1–99
 - Si/SiO₂ system 74–96
 - DRAM (dynamic random access memory) 80–82
 - DRAM storage capacitor 82–90
 - MOSFETs 77–80
 - sidewall doping 95
 - simulated annealing 315
 - simulation
 - -based engineering science 290–291
 - device/process 298–299
 - KMC 300–304, 307, 309
 - molecular 298–304
 - multiscale, *see* multiscale simulation
 - QM 305–306
 - shape change 146, 150, 167
 - stochastic codes 316
 - single-crystal electrodes, macroscopic 29
 - single-ring Co porphyrin 255–259
 - single-step dipping 72
 - single Ti/TiO₂ grains 18–19
 - anodic passive layer formation 28–30
 - sinter aid 72
 - sinter body, anode 71–72
 - sinter conditions, Ta capacitors 67–70
 - sintered powder technology 54, 63–64
 - sintering 97
 - Nb/Nb₂O₅ system 52
 - Y- 69
 - site dependence, charge transfer kinetics 142–143
 - slow desorption 222
 - slow pyrolysis–mass spectra 276
 - smoothing mechanisms 110–113
 - solid–liquid interface 307
 - solution phase transition metal macrocycles, intrinsic properties 204–212
 - solution phase voltammogram 266
 - space charge layer 7, 13, 57
 - space charge polarization 59
 - speciation
 - molecular 209–211
 - redox 235–238
 - spectra
 - electron spin resonance 203
 - photocurrent, *see* photocurrent spectra
 - pyrolysis–mass spectra 276–277
 - UV–visible 210
 - XPS 51
 - XRD 96
 - spectroscopy
 - electrohydrodynamic impedance 127
 - *in situ* 281–283
 - micro-reflection 22–23

- Mössbauer effect 276–277
 - quasi *in situ* 281–283
 - redox active electrodes 233–235
 - spectroscopic anisotropy micro-ellipsometry, *see* SAME
 - thermally activated macrocycles 275–281
 - X-ray absorption fine structure 278–281
 - XPS 51, 281
 - spin resonance spectra, electron 203
 - sponge-like structure 52, 63–64, 97
 - spontaneous adsorption 221–223
 - SPS (sulfonate-terminated disulfide) 135–148, 164–178, 313–314
 - adsorption 143–145, 164
 - stability analysis
 - catalyst-derived brightening 173–175
 - geometric leveling 160–161
 - stabilization
 - across length scales 112–113
 - superconformal film growth 110–113
 - stack-capacitor DRAMs 91
 - standard hydrogen electrode, *see* SHE
 - standard reduction potential 193, 195
 - steady state polarization curves 198, 249
 - steady state ring-disk polarization curves 272–273
 - STI (shallow trench isolation) 77, 84
 - stochastic simulation codes 316
 - storage capacitor, DRAM, *see* DRAM
 - strongly adsorbed surfactant 118
 - structural properties
 - modified electrodes 232–235
 - thermally activated macrocycles 275–281
 - sub-micrometer trenches 108
 - substrate grain orientation, Ti 17–18
 - substrate texture 37
 - sulfonate-terminated disulfide, *see* SPS
 - supercapacitor 58–59, 73
 - superconformal film growth 107–179
 - additive processes 113–146
 - destabilizing influences 108–110
 - interface motion 146, 178
 - morphological evolution 146, 178
 - stabilization 110, 114
 - superfilling 107–109, 157–158, 165–174
 - vias 170–171
 - superleveling 163
 - surface mounted devices 65
 - surface segregation 117–121
 - surface states, number of 76
 - surfaces, rough 109
 - rough 314
 - surfactant, strongly adsorbed 118
 - susceptibility, molar paramagnetic 212
 - synchrotron radiation 230
 - synergistic interactions 122
 - systems engineering, multiscale 291
- t**
- Ta capacitors 62–66
 - dislocation formation 67–70
 - Ta/Ta₂O₅ system 54–57
 - Tafel plots 34, 247
 - Tafel slope 248
 - Ta₂O₅, DT technology 92–95
 - Teflon-bonded electrode 279
 - temperature distribution, Gaussian 9
 - texture, Zr/ZrO₂ substrate 37
 - texture dependence
 - HfO₂ film formation 48
 - ZrO₂ film formation 40
 - thermal activation, transition metal macrocycles 269–283
 - thermal annealing 68–69
 - rapid 93, 317–318
 - thermal conductivity, anode sinter body 71–72
 - thermal effects, lasers 9–10
 - thermal nitridation, rapid 90
 - thermal runaway, Ta capacitors 70–74
 - thermodynamic aspects, redox active electrodes 232–235
 - thickness
 - boundary layer, *see* boundary layer thickness
 - film, *see* film thickness
 - hydrodynamic boundary layer, *see* hydrodynamic boundary layer thickness
 - thin film dielectrics, electroceramic 46
 - thin layer electrode, optically transparent 206–212
 - thin porous coating electrodes 269, 271
 - threshold current 160
 - through-mask plating 114
 - Ti substrate grain orientation 17–18
 - Ti/TiO₂ system 15–37
 - DT technology 95–96
 - heterogeneity 15
 - single grains 18–19
 - time-dependent diffusion equation 148
 - time scales, multiple 293
 - TiO₂, photocurrent model 11–15
 - TiO₂ films
 - microscopic modification 19–21
 - modified 21–25
 - trans*-[Co([14]aneN₄)(OH₂)₂]³⁺ 212–216
 - transfer coefficient, cation 3
 - transient measurements 33–34
 - transients, chronoamperometric 137–138, 141

- transistors, metal oxide semiconductor field effect, *see* MOSFETs
 - transition metal macrocycles 191–284
 - diffusion coefficients 204–205
 - electrocatalytic properties 201–204
 - fundamentals 199–201
 - heterogeneous electrocatalysis 219–268
 - homogeneous electrocatalysis 204–219
 - solution phase 204–212
 - thermal activation 269–283
 - transition metal phthalocyanines 244–247
 - transition probabilities 302
 - transport, intra-layer 109
 - trenches
 - deep, *see* DT
 - filling 166, 168–170
 - filling simulations 148
 - sub-micrometer 108
 - tunneling
 - direct 81
 - direct/resonance 35
 - Fowler–Nordheim 81
- u**
- ultra-thin amorphous films, photocurrent model 11–15
 - unmetallated macrocycles 200
 - UV-laser scanning analysis 21–22
 - UV–visible reflectance 233
 - UV–visible spectra 210
- v**
- V-doping 51
 - V-notch groove 151
 - valve metal systems
 - Al/Al₂O₃ system 53–54
 - electrolytic capacitor manufacturing 57–74
 - Hf/HfO₂ system 46–48
 - Nb/Nb₂O₅ system 49–53
 - Ta/Ta₂O₅ system 54–57
 - Ti/TiO₂ 15–37
 - Zr/ZrO₂ system 37–46
 - valve metals
 - as dielectric films 1–99
 - electrochemical oxide layer formation 5–7
 - electrode $C(U)$ curves 7–8
 - vias 164–165, 170–172
 - vibrational properties, modified electrodes 229–230
 - void formation 170
 - Volmer
 - Butler–Volmer equation 238
 - Butler–Volmer kinetics 148
 - voltammetry 114, 122, 136–137, 146
 - differential pulse 225, 238
 - multicycle 144
 - voltammogram
 - cyclic, *see* cyclic voltammogram
 - hysteretic 136
 - solution phase 266
- w**
- wavenumber, critical 175
- x**
- X-ray absorption fine structure spectroscopy 277–281
 - XANES (X-ray absorption near edge structure) 230–231, 235, 237, 275–281
 - XPS (X-ray photoelectron spectroscopy) 281
 - spectra 51
 - XRD (X-ray diffraction) analysis 53–54
 - XRD (X-ray diffraction) spectra 96
- y**
- Y-sintering 69
 - yield, quantum, *see* quantum yield
- z**
- Zr/ZrO₂ system 37–46